TOSHIBA Transistor Silicon NPN Epitaxial Type (Darlington power transistor)

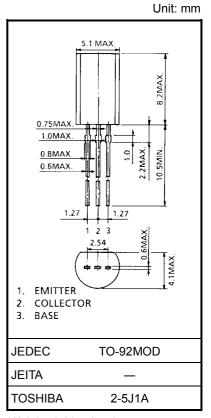
2SD2536

Switching Applications Micro Motor Drive, Hammer Drive Applications

- High DC current gain: $h_{FE} = 2000$ (min) ($V_{CE} = 2 V$, $I_{C} = 1 A$)
- Low saturation voltage: VCE (sat) = 1.2 V (max)
 (IC = 0.7 A, VBH = 4.2 V)
- · Zener diode included between collector and base.

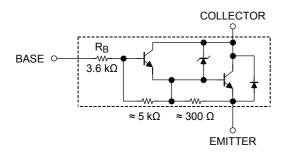
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	85	V	
Collector-emitter voltage	V_{CEO}	100 ± 15	V	
Emitter-base voltage	V _{EBO}	6	V	
Bias voltage	V _B	20	V	
Collector current	IC	2	Α	
Collector power dissipation	PC	0.9	W	
Base current	ΙΒ	0.5	Α	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	−55 to 150	°C	



Weight: 0.36 g (typ.)

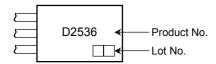
Equivalent Circuit



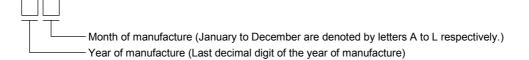
Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I _{CBO}	V _{CB} = 80 V, I _E = 0	_	_	10	μA
Emitter cut-off cu	rrent	I _{EBO}	V _{EB} = 6 V, I _C = 0	0.3	_	1.5	mA
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	85	100	115	V
Base resistance		R _B	_	2.5	3.6	4.7	kΩ
DC current gain		h _{FE}	V _{CE} = 2 V, I _C = 1 A	2000	_	_	
Collector-emitter saturation voltage		V _{CE} (sat) (1)	I _C = 0.7 A, V _{BH} = 4.2 V	_	_	1.2	V
		V _{CE} (sat) (2)	I _C = 1 A, V _{BH} = 4.2 V	_	_	1.5	
Input threshold voltage		V_{BL}	V _{CE} = 50 V, I _C = 100 μA	_	_	0.7	V
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	20	_	pF
Unclamped inductive load energy		E _{S/B}	L = 10 mH, I _C = 1 A, V _{BH} = 10 V	5	_	_	mJ
Switching time	Turn-on time	t _r	Output 0 Input $0 \text{ VBH} = 5 \text{ V}$ $V_{CC} = 30 \text{ V}$ Duty cycle $\leq 1\%$	_	0.3	_	μs
	Storage time	t _{stg}		_	4.0	_	
	Fall time	t _f		_	0.6	_	

Marking



Explanation of Lot No.



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